

# Brian R Wier

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Reliability Differences Between SiGe HBTs Optimized for High-Performance and Medium-Breakdown. , 2019, , .		1
2	Limiting Effects on the Design of Vertical Superjunction Collectors in SiGe HBTs. IEEE Transactions on Electron Devices, 2018, 65, 793-797.	3.0	0
3	Hot-Carrier-Damage-Induced Current Gain Enhancement (CGE) Effects in SiGe HBTs. IEEE Transactions on Electron Devices, 2018, 65, 2430-2438.	3.0	11
4	Revisiting Safe Operating Area: SiGe HBT Aging Models for Reliability-Aware Circuit Design. , 2018, , .		2
5	Collector Transport in SiGe HBTs Operating at Cryogenic Temperatures. IEEE Transactions on Electron Devices, 2018, 65, 3697-3703.	3.0	15
6	SiGe HBT Profiles With Enhanced Inverse-Mode Operation and Their Impact on Single-Event Transients. IEEE Transactions on Nuclear Science, 2018, 65, 399-406.	2.0	9
7	Operation of SiGe HBTs Down to 70 mK. IEEE Electron Device Letters, 2017, 38, 12-15.	3.9	28
8	Physical Differences in Hot Carrier Degradation of Oxide Interfaces in Complementary (n-p-n+p-p-n-p) SiGe HBTs. IEEE Transactions on Electron Devices, 2017, 64, 37-44.	3.0	10
9	Modeling of high-current damage in SiGe HBTs under pulsed stress. , 2016, , .		3
10	A Physics-Based Circuit Aging Model for Mixed-Mode Degradation in SiGe HBTs. IEEE Transactions on Electron Devices, 2016, 63, 2987-2993.	3.0	15
11	The Role of Negative Feedback Effects on Single-Event Transients in SiGe HBT Analog Circuits. IEEE Transactions on Nuclear Science, 2015, 62, 2599-2605.	2.0	4
12	Bias- and Temperature-Dependent Accumulated Stress Modeling of Mixed-Mode Damage in SiGe HBTs. IEEE Transactions on Electron Devices, 2015, 62, 2084-2091.	3.0	19
13	A Comparison of Field and Current-Driven Hot-Carrier Reliability in NPN SiGe HBTs. IEEE Transactions on Electron Devices, 2015, 62, 2244-2250.	3.0	19
14	Large-Signal Reliability Analysis of SiGe HBT Cascode Driver Amplifiers. IEEE Transactions on Electron Devices, 2015, 62, 1383-1389.	3.0	28
15	On the reliability of SiGe HBT cascode driver amplifiers. , 2014, , .		3
16	A 0.8 THz $f_{m\text{ MAX}}$ SiGe HBT Operating at 4.3 K. IEEE Electron Device Letters, 2014, 35, 151-153.	3.9	60